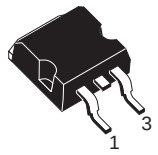
STB9NC60
STB9NC60-1

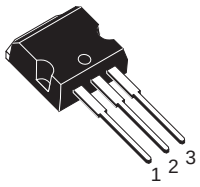
N-CHANNEL 600V - 0.6Ω - 9A - D^2PAK/I^2PAK
PowerMesh™II MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STB9NC60	600 V	< 0.75 Ω	9.0 A
STB9NC60-1	600 V	< 0.75 Ω	9.0 A

- TYPICAL $R_{DS}(on)$ = 0.6 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED



D^2PAK



I^2PAK

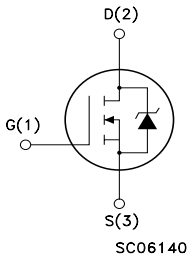
DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns swithing speed, gate charge and ruggedness.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVER

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate- source Voltage	±30	V
I_D	Drain Current (continuos) at T_C = 25°C	9	A
I_D	Drain Current (continuos) at T_C = 100°C	5.7	A
I_{DM} (1)	Drain Current (pulsed)	36	A
P_{TOT}	Total Dissipation at T_C = 25°C	125	W
	Derating Factor	1.0	W/°C
dv/dt	Peak Diode Recovery voltage slope	3.5	V/ns
T_{stg}	Storage Temperature	– 55 to 150	°C
T_j	Max. Operating Junction Temperature		

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤9A, di/dt ≤100A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.0	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	9	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	850	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			50	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 4.5 A		0.6	0.75	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} =20 V , I_D = 4.5A		9		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1420		pF
C_{oss}	Output Capacitance			205		pF
C_{rss}	Reverse Transfer Capacitance			35		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 300V, I_D = 4.5 A R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		20		ns
t_r	Rise Time			16		ns
Q_g	Total Gate Charge	V_{DD} = 480V, I_D = 9.0 A, V_{GS} = 10V		55	77	nC
Q_{gs}	Gate-Source Charge			4.5		nC
Q_{gd}	Gate-Drain Charge			31		nC

SWITCHING OFF

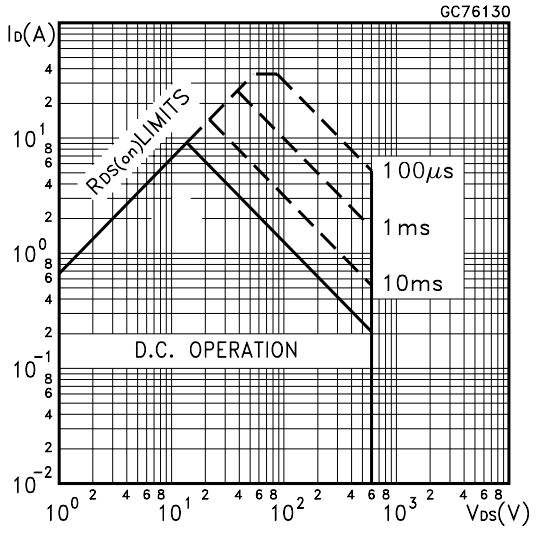
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 300 V, I_D = 4.5 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		64 32		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 480V, I_D = 9.0 A, R_G = 4.7Ω, V_{GS} = 10V (Inductive Load see, Figure 5)		19 13 32		ns ns ns

SOURCE DRAIN DIODE

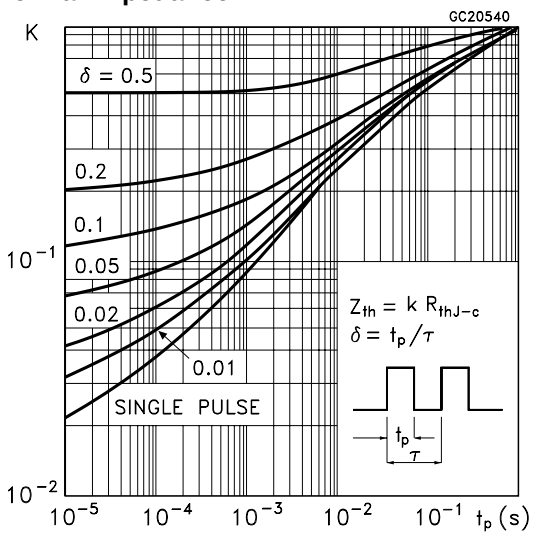
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				9.0	A
I_{SDM} (2)	Source-drain Current (pulsed)				36	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 9 A, V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 9 A, di/dt = 100A/µs, V_{DD} = 100V, Tj = 150°C (see test circuit, Figure 5)		600		ns
Q_{rr}	Reverse Recovery Charge			4.7		µC
I_{RRM}	Reverse Recovery Current			15.5		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

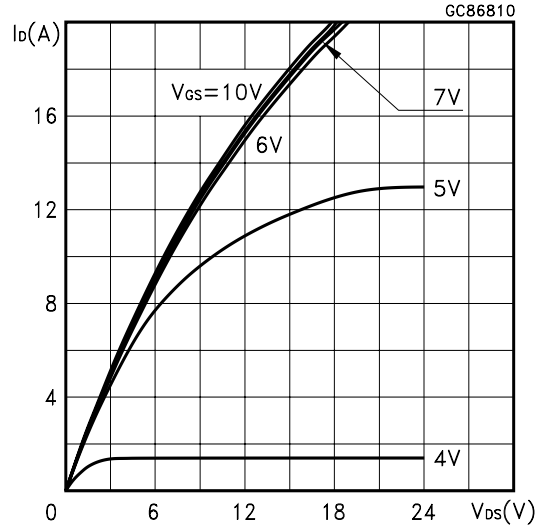
Safe Operating Area



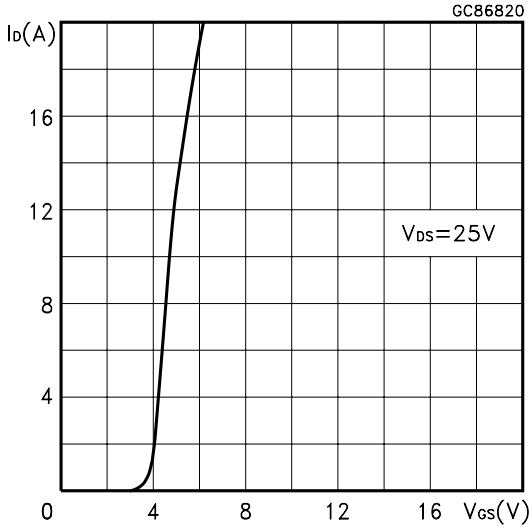
Thermal Impedance



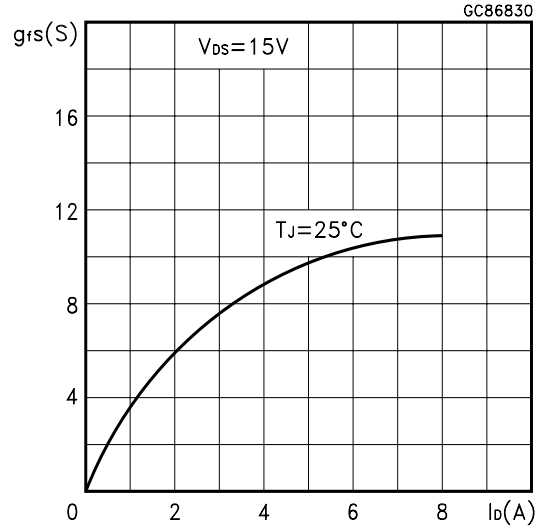
Output Characteristics



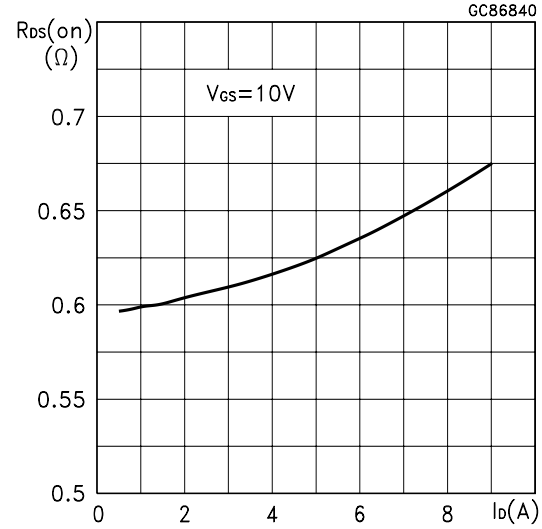
Transfer Characteristics



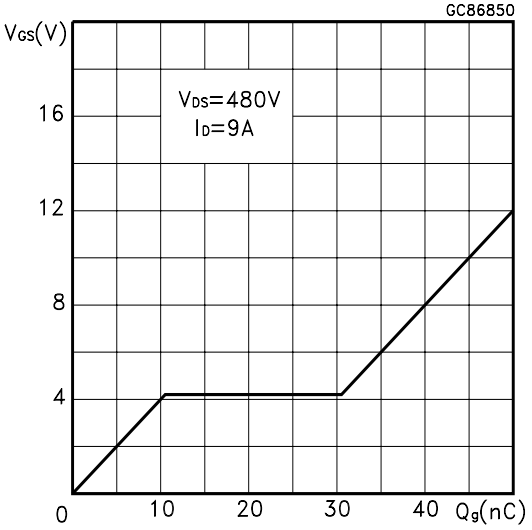
Transconductance



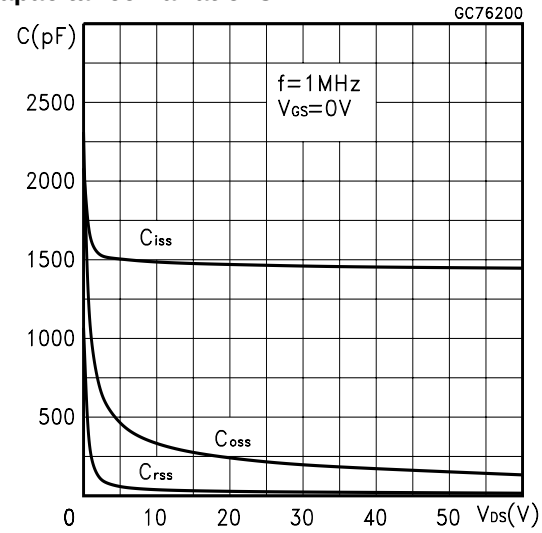
Transconductance



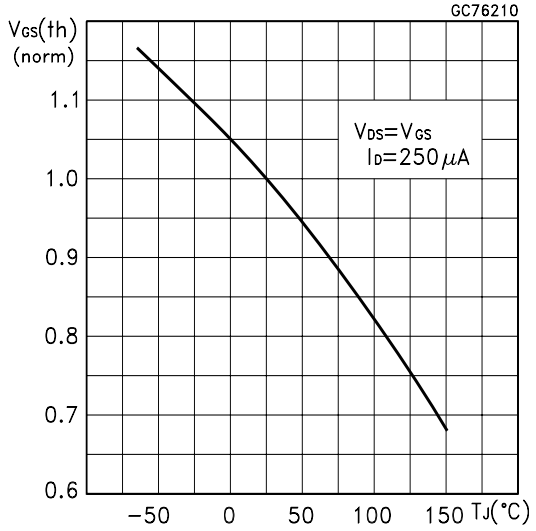
Gate Charge vs Gate-source Voltage



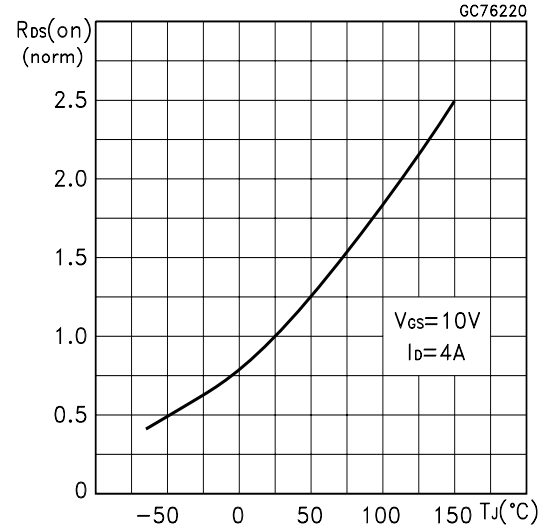
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

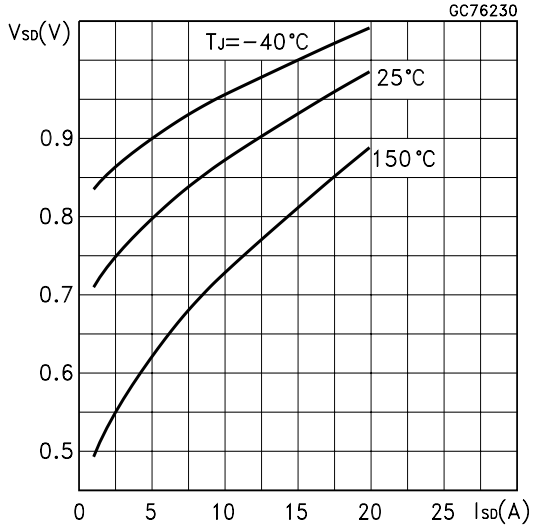


Fig. 1: Unclamped Inductive Load Test Circuit

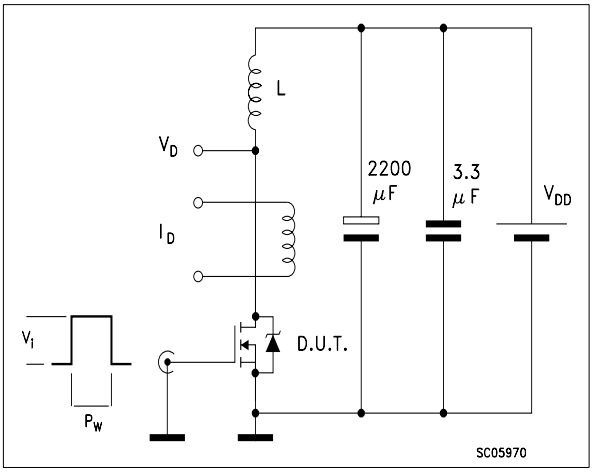


Fig. 2: Unclamped Inductive Waveform

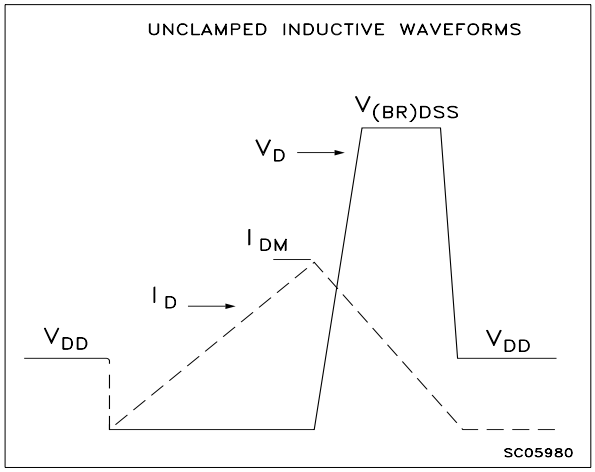


Fig. 3: Switching Times Test Circuit For Resistive Load

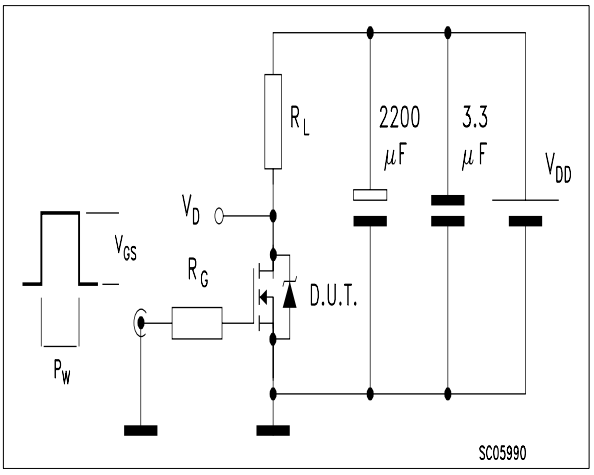


Fig. 4: Gate Charge test Circuit

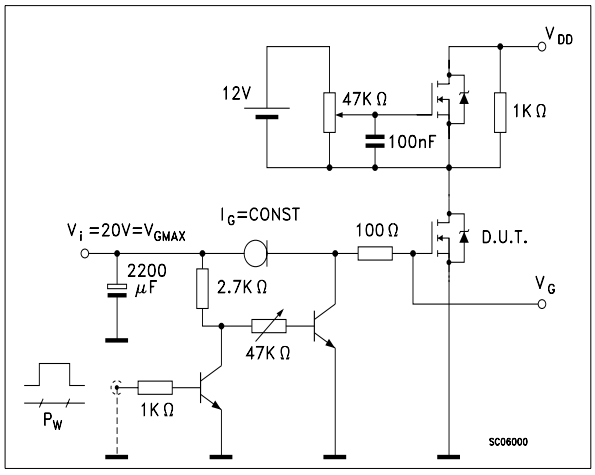
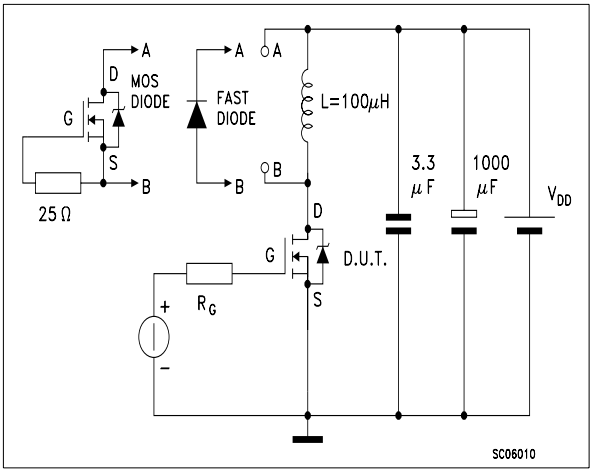
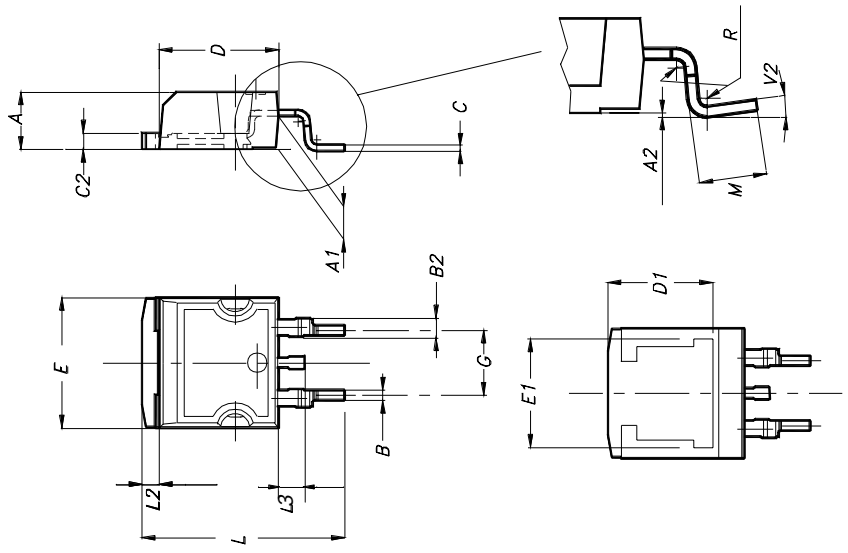


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



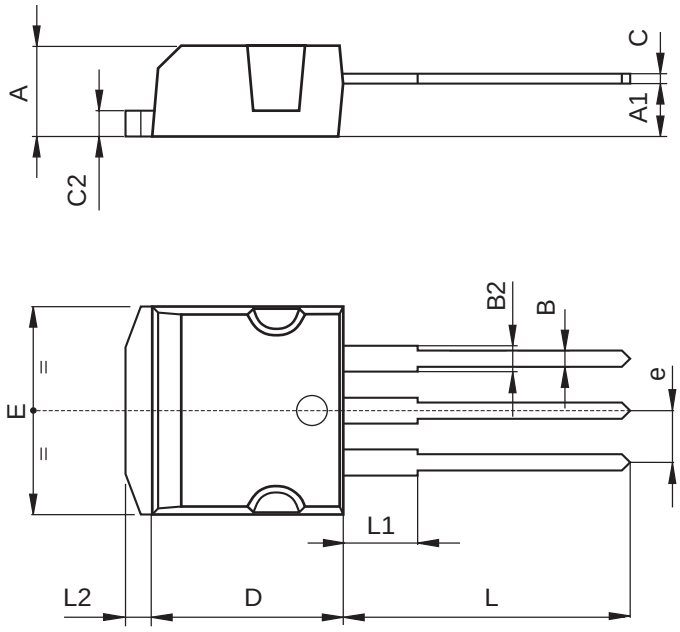
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º			



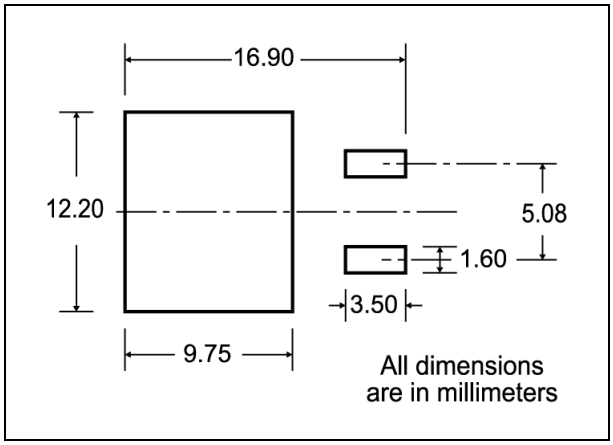
TO-262 (I^2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

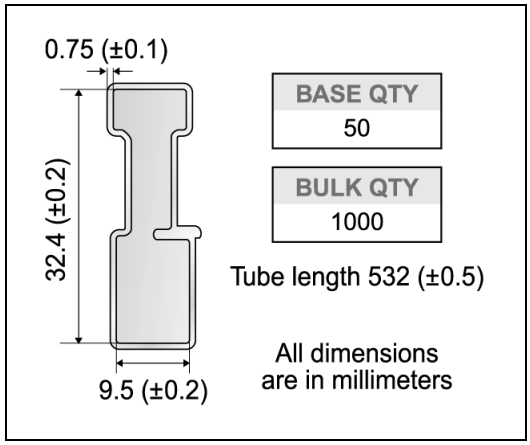


P011P5/E

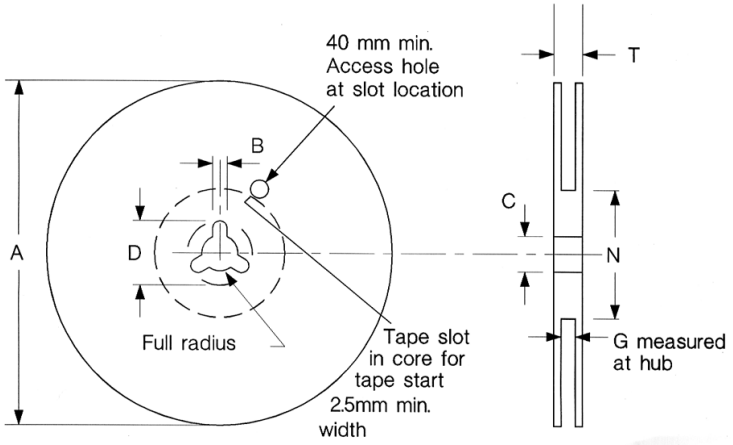
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



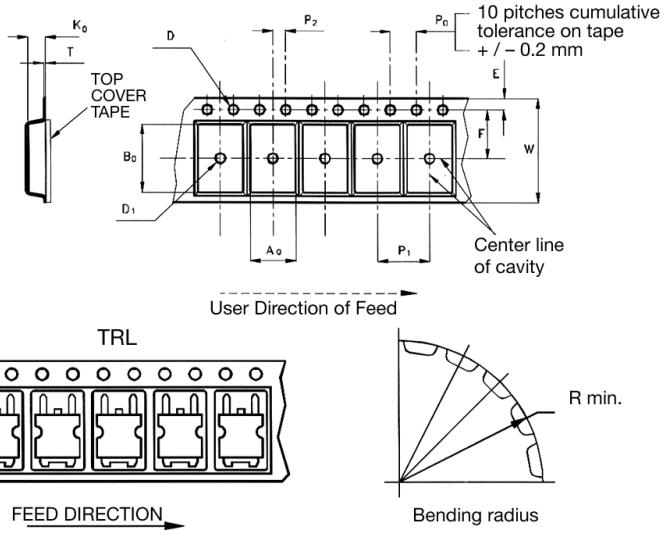
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

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